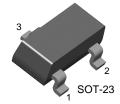


KST4401

Switching Transistor



1. Base 2. Emitter 3. Collector

NPN Epitaxial Silicon Transistor

Absolute Maximum Ratings T_a=25°C unless otherwise noted

Symbol	Parameter	Value	Units
V_{CBO}	Collector-Base Voltage	60	V
V _{CEO}	Collector-Emitter Voltage	40	V
V_{EBO}	Emitter-Base Voltage	6	V
I _C	Collector Current	600	mA
P _C	Collector Dissipation	350	mW
T _{STG}	Storage Temperature	150	°C

$\textbf{Electrical Characteristics} \ \, \textbf{T}_{a} \!\!=\!\! 25^{\circ} \textbf{C} \ \, \text{unless otherwise noted}$

Symbol	Parameter	Test Condition	Min.	Max.	Units
BV _{CBO}	Collector-Base Breakdown Voltage	I _C =100μA, I _E =0	60		V
BV _{CEO}	* Collector-Emitter Breakdown Voltage	I _C =1.0mA, I _B =0	40		V
BV _{EBO}	Emitter-Base Breakdown Voltage	I _E =100μA, I _C =0	6		V
I _{BEV}	Base Cut-off Current	V _{CE} =35V, V _{EB} =0.4V		100	nA
I _{CEX}	Collector Cut-off Current	V _{CE} =35V, V _{EB} =0.4V		100	nA
h _{FE}	* DC Current Gain	$\begin{array}{c} V_{CE} = 1 \text{V, } I_{C} = 0.1 \text{mA} \\ V_{CE} = 1 \text{V, } I_{C} = 1 \text{mA} \\ V_{CE} = 1 \text{V, } I_{C} = 10 \text{mA} \\ V_{CE} = 1 \text{V, } I_{C} = 150 \text{mA} \\ V_{CE} = 2 \text{V, } I_{C} = 500 \text{mA} \end{array}$	20 40 80 100 40	300	
V _{CE} (sat)	* Collector-Emitter Saturation Voltage	I _C =150mA, I _B =15mA I _C =500mA, I _B =50mA		0.4 0.75	V V
V _{BE} (sat)	* Base-Emitter Saturation Voltage	I _C =150mA, I _B =15mA 0.75 I _C =500mA, I _B =50mA		0.95 1.2	V V
f _T	Current Gain Bandwidth Product	I _C =20mA, V _{CE} =10V 250 f=100MHz			MHz
C _{ob}	Output Capacitance	V _{CB} =5V, I _E =0, f=100KHz 6.5		6.5	pF
t _{ON}	Turn On Time	V _{CC} =30V, V _{BE} =2V 35 I _C =150mA, I _{B1} =15mA		35	ns
t _{OFF}	Turn Off Time	V _{CC} =30V, I _C =150mA 255 I _{B1} =I _{B2} =15mA		255	ns

^{*} Pulse Test: Pulse Width≤300μs, Duty Cycle≤2%



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Typical Characteristics

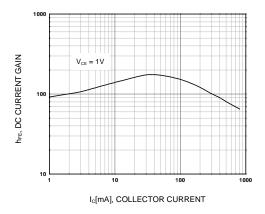


Figure 1. DC current Gain

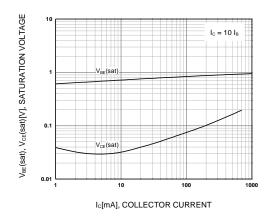


Figure 2. Collector-Emitter Saturation Voltage Base-Emitter Saturation Voltage

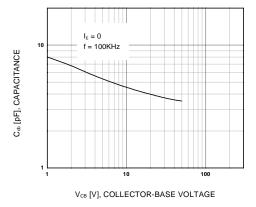


Figure 3. Collector-Base Capacitance

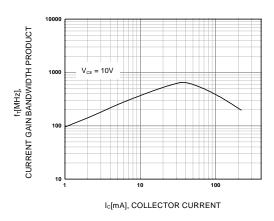
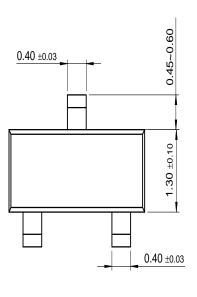
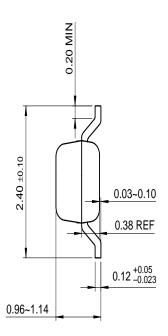


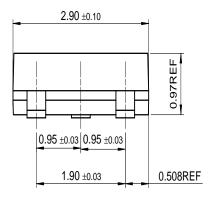
Figure 4. Current Gain Bandwidth Product

Package Dimensions

SOT-23







Dimensions in Millimeters

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